

ABSTRACT OF THE DISCLOSURE

A method of enabling the removal of fluorine containing residue from a semiconductor substrate comprising applying a gas and/or vapor to which the residue is reactive to the residue while the temperature of the substrate is at an elevated level with respect to ambient temperature and the residue is exposed to ultraviolet radiation, for a time period which is sufficient to effect at least one of volatilizing the residue or rendering the residue hydrophilic enough to be removable with deionized water.